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GJ1182 PNP SILICON EPITAXIAL PLANAR TRANSISTOR

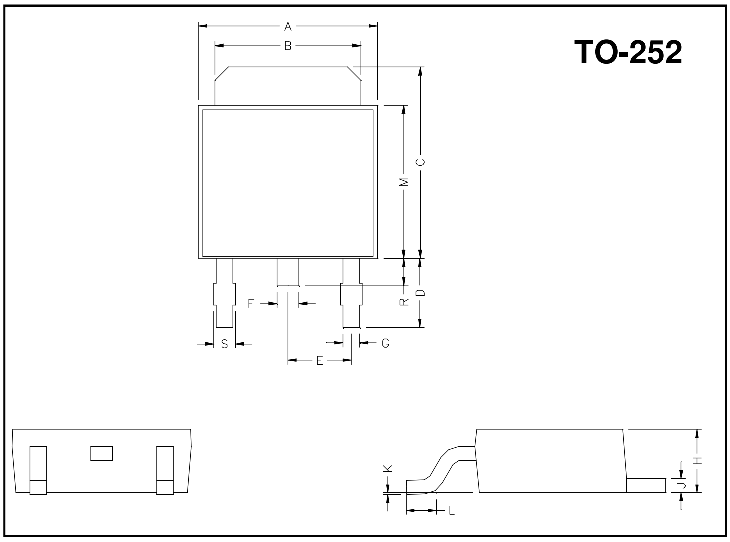
Description

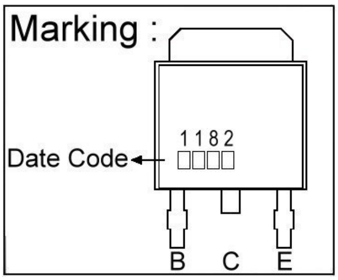
The GJ1182 is designed for medium power amplifier applications.

Features

- Low collector saturation voltage : $V_{CE(sat)}$=-0.5V(Typ.)

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Collector Current (Pulse, Pw=100ms)	I_C	-3	A
Total Power Dissipation(T_C=25℃)	P_D	10	W

Electrical Characteristics (Ta = 25℃, unless otherwise noted)

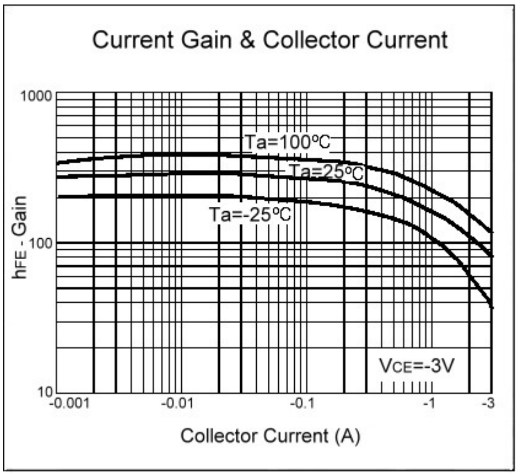
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-50uA , I_E=0
BV_{CEO}	-32	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-50uA ,I_C=0
I_{CBO}	-	-	-1	uA	V_{CB}=-20V, I_E=0
I_{EBO}	-	-	-1	uA	V_{EB}=-4V, I_C=0
*$V_{CE(sat)}$	-	-500	-800	mV	I_C=-2A, I_B=-200mA
*h_{FE}	82	-	390		V_{CE}=-3V, I_C=-500mA
fT	-	100	-	MHz	V_{CE}=-5V, I_C=-500mA, f=100MHz
Cob	-	50	-	pF	V_{CB}=-10V, I_E=0, f=1MHz

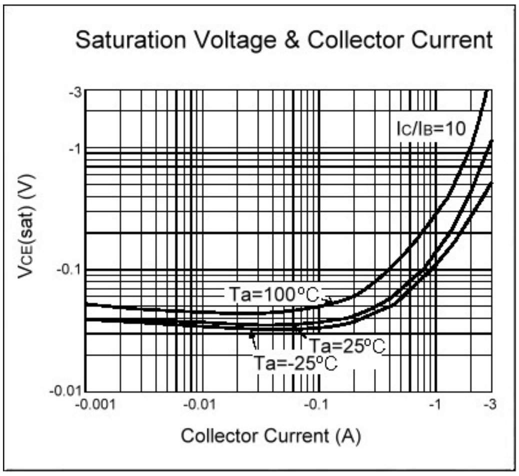
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

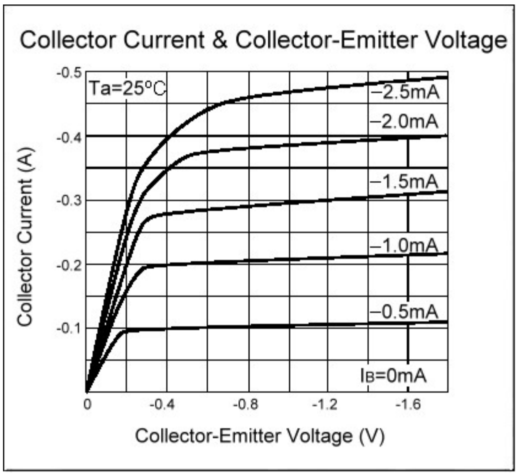
Classification Of h_{FE}

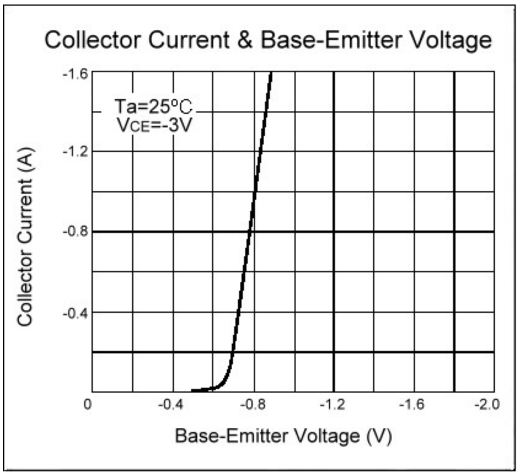
Rank	P	Q	R
Range	**82 ~ 180**	**120 ~ 270**	**180 ~ 390**

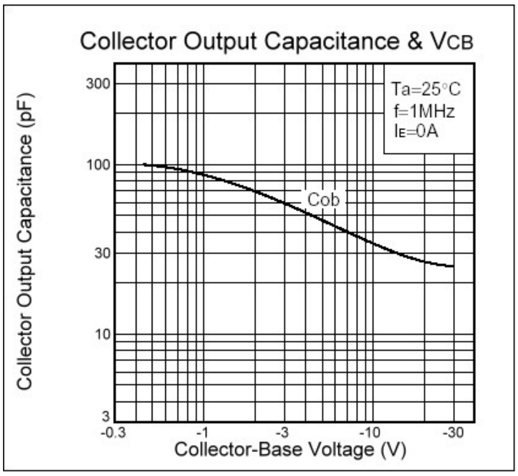
Characteristics Curve

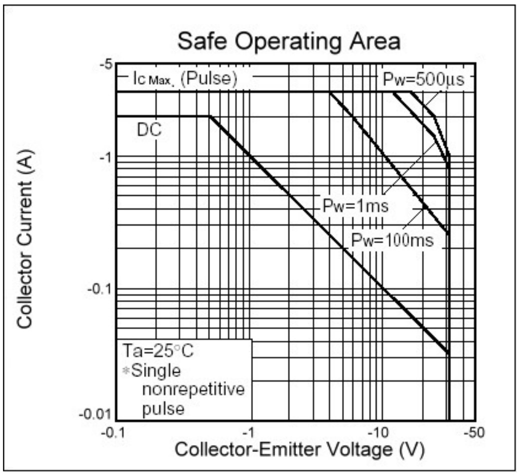












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